

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1803 is a switching device which can be driven directly by a 4.5 V power source.

The μ PA1803 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 4.5 V power source
- Low on-state resistance $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX.}$ (VGs = 10 V, ID = 4.0 A) $R_{DS(on)2} = 16 \text{ m}\Omega \text{ MAX.}$ (VGs = 4.5 V, ID = 4.0 A)
- · Built-in G-S protection diode against ESD

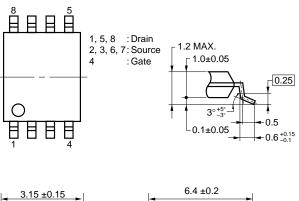
ORDERING INFORMATION

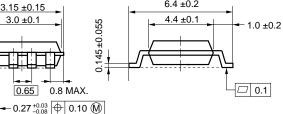
| PART NUMBER | PACKAGE |
|---------------|--------------|
| μPA1803GR-9JG | Power TSSOP8 |

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

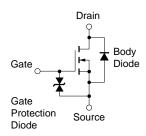
| Drain to Source Voltage | VDSS | 30 |
|-------------------------------|----------|-------------|
| Gate to Source Voltage | Vgss | ±20 |
| Drain Current (DC) | D(DC) | ±8.0 |
| Drain Current (pulse) Note1 | D(pulse) | ±32 |
| Total Power Dissipation Note2 | Рт | 2.0 |
| Channel Temperature | Tch | 150 |
| Storage Temperature | Tstg | -55 to +150 |







EQUIVALENT CIRCUIT



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on ceramic substrate of 5000 mm² x 1.1 mm
- **Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

V

V A

A W

°C

°C

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The mark <R> shows major revised points.

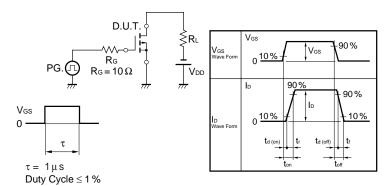


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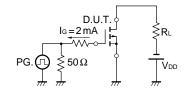
| ELECTRICAL | CHARACTERISTICS | $(T_A = 25^{\circ}C)$ |
|------------|-----------------|-----------------------|
|------------|-----------------|-----------------------|

| CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|--|------|------|------|------|
| Zero Gate Voltage Drain Current | loss | V _{DS} = 30 V, V _{GS} = 0 V | | | 10 | μA |
| Gate Leakage Current | lgss | $V_{GS} = \pm 20 V, V_{DS} = 0 V$ | | | ±10 | μA |
| Gate to Source Cut-off Voltage | V _{GS(off)} | V _{DS} = 10 V, I _D = 1 mA | 1.5 | 1.9 | 2.5 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} = 10 V, I _D = 4.0 A | 3 | 14 | | s |
| Drain to Source On-state Resistance | RDS(on)1 | $V_{GS} = 10 V$, $I_D = 4.0 A$ | | 8.6 | 12 | mΩ |
| | RDS(on)2 | V_{GS} = 4.5 V, I _D = 4.0 A | | 11 | 16 | mΩ |
| Input Capacitance | Ciss | V _{DS} = 10 V, | | 1880 | | pF |
| Output Capacitance | Coss | V _{GS} = 0 V, | | 571 | | pF |
| Reverse Transfer Capacitance | Crss | f = 1 MHz | | 214 | | pF |
| Turn-on Delay Time | td(on) | V _{DD} = 15 V, | | 27 | | ns |
| Rise Time | tr | I _D = 4.0 A, | | 77 | | ns |
| Turn-off Delay Time | td(off) | V _{GS} = 10 V, | | 72 | | ns |
| Fall Time | tr | R _G = 10 Ω | | 47 | | ns |
| Total Gate Charge | Q _G | V _{DD} = 24 V, | | 36 | | nC |
| Gate to Source Charge | Q _{GS} | I _D = 8.0 A, | | 5.1 | | nC |
| Gate to Drain Charge | Qgd | V _{GS} = 10 V | | 8.7 | | nC |
| Diode Forward Voltage | VF(S-D) | IF = 8.0 A, V _{GS} = 0 V | | 0.78 | | V |
| Reverse Recovery Time | trr | IF = 8.0 A, VGS = 0 V, | | 37 | | ns |
| Reverse Recovery Charge | Qrr | di/dt = 100 A / μs | | 35 | | nC |

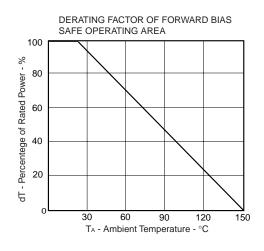
TEST CIRCUIT 1 SWITCHING TIME



TEST CIRCUIT 2 GATE CHARGE



TYPICAL CHARACTERISTICS (T_A = 25°C)



DRAIN CURRENT vs.

Vgs = 10 V

-4.5 V

0.4

25

20

15

10

5

0

0.2

lo - Drain Current - A

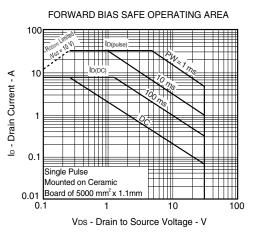
DRAIN TO SOURCE VOLTAGE

0.6

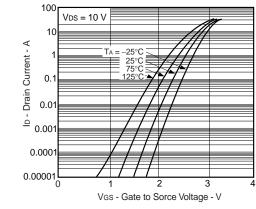
VDS - Drain to Source Voltage - V

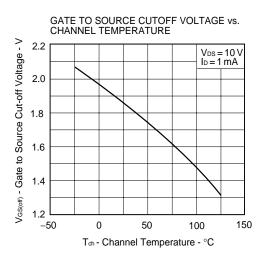
0.8

1.0

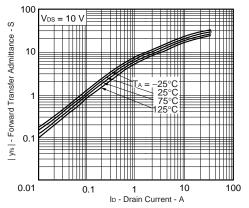


TRANSFER CHARACTERISTICS

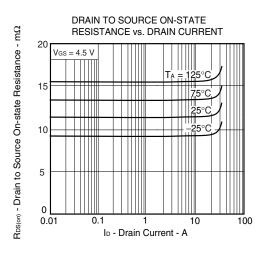


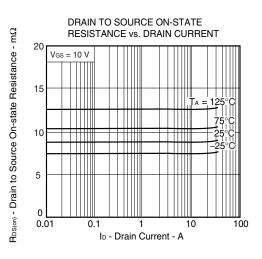


FORWARD TRANSFER ADMITTANCE Vs. DRAIN CURRENT

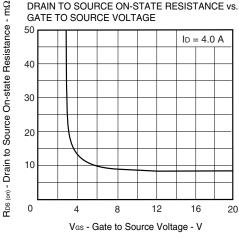


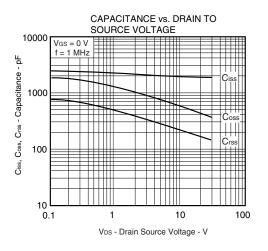
3

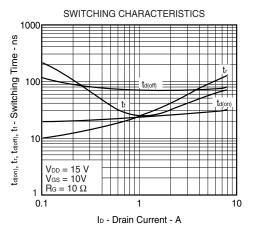




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE





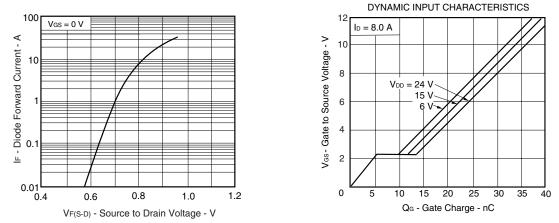


 $R_{DS (on)}$ - Drain to Source On-state Resistance - $m\Omega$ CHANNEL TEMPERATURE 20 ID = 4.0 A $V_{GS} = 4.5 V$ 10 V 10 0 100 -50 0 50 150 Tch - Channel Temperature - °C

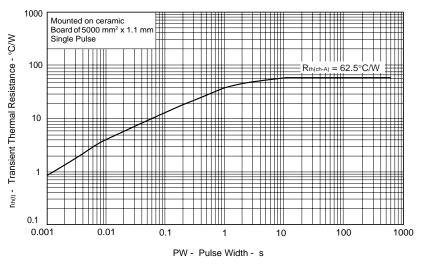
DRAIN TO SOURCE ON-STATE RESISTANCE vs.

4

SOURCE TO DRAIN DIODE FORWARD VOLTAGE







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